Ain Shams University
Faculty of Education
Department of Physics

"Study the physical properties of $ZnIn_2Se_4$ for photovoltaic applications"

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By

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بسم الله الرحمن الرحيم

" سبحانك لا علم لنا إلا ما علمتنا
انك أنت العليم الحكيم"

صدق الله العظيم

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